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RSC Advances Supporting Information

Critical role of silk fibroin secondary structure on the dielectric performances of organic thin-film transistors

Min Hong Park,[a†] Junhyung Kim,[b†] Seung Chul Lee,[b] Se Youn Cho,[a] Na Rae Kim,[a] Boseok Kang,[c] Eunjoo Song,[c] Kilwon Cho,[c] Hyoung-Joon Jin,[a*] and Wi Hyoung Lee,[ba)*]

[a]Department of Polymer Science and Engineering, Inha University, Incheon 402-751, Korea

[b]Department of Organic and Nano System Engineering, Konkuk University, Seoul 143-701, Korea

[c]Department of Chemical Engineering, Pohang University of Science and Technology, Pohang 790-784, Korea

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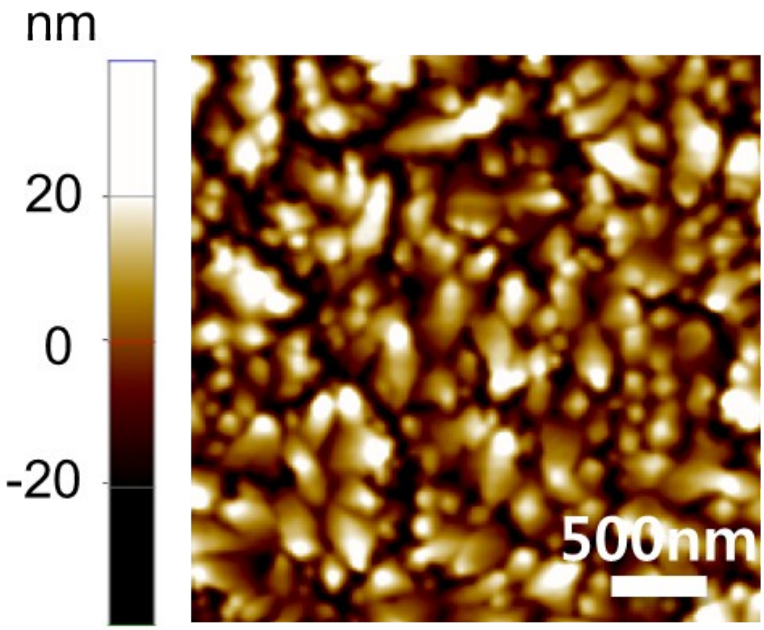
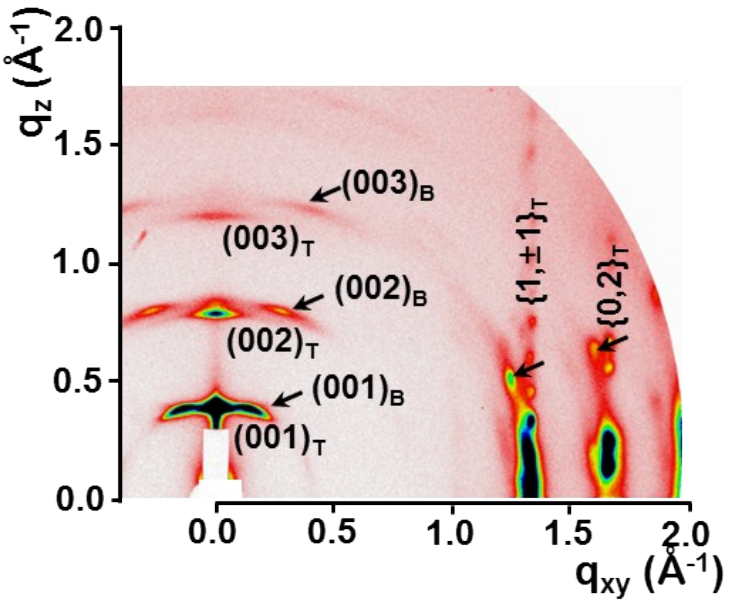
† M. H. Park and J. Kim contributed equally to this work.

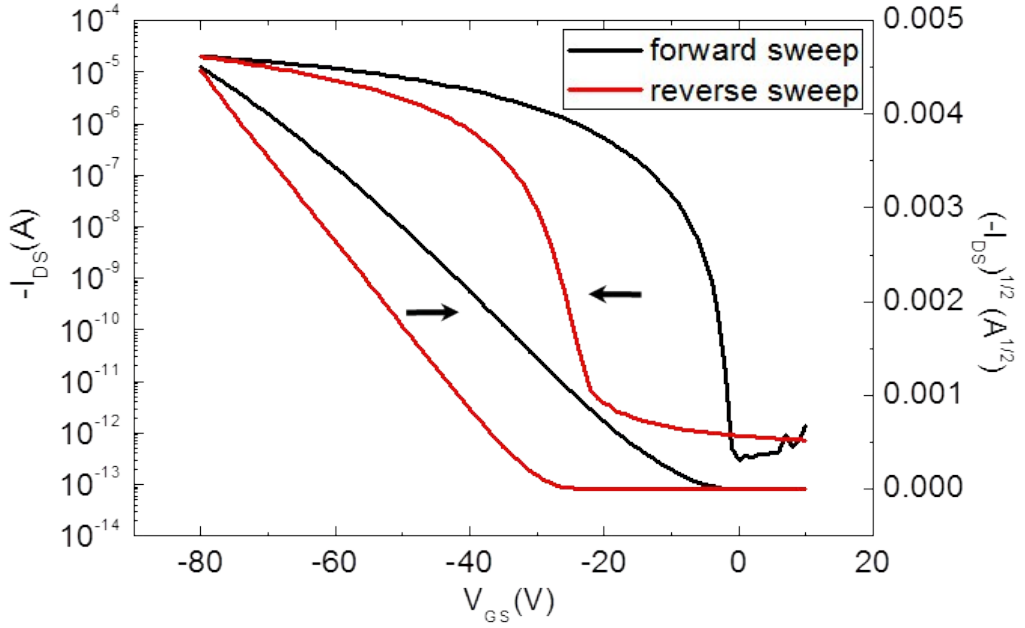
* Corresponding authors E-mail: hjjin@inha.ac.kr, whlee78@konkuk.ac.kr



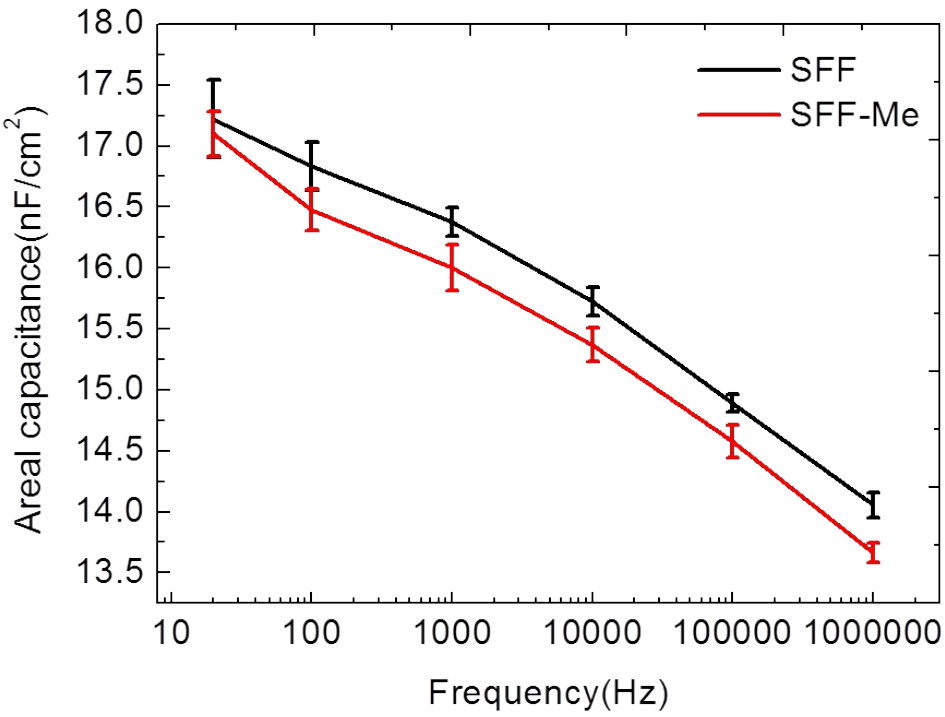
Supporting Figure S1. AFM image of pentacene film on SiO_2 dielectric.



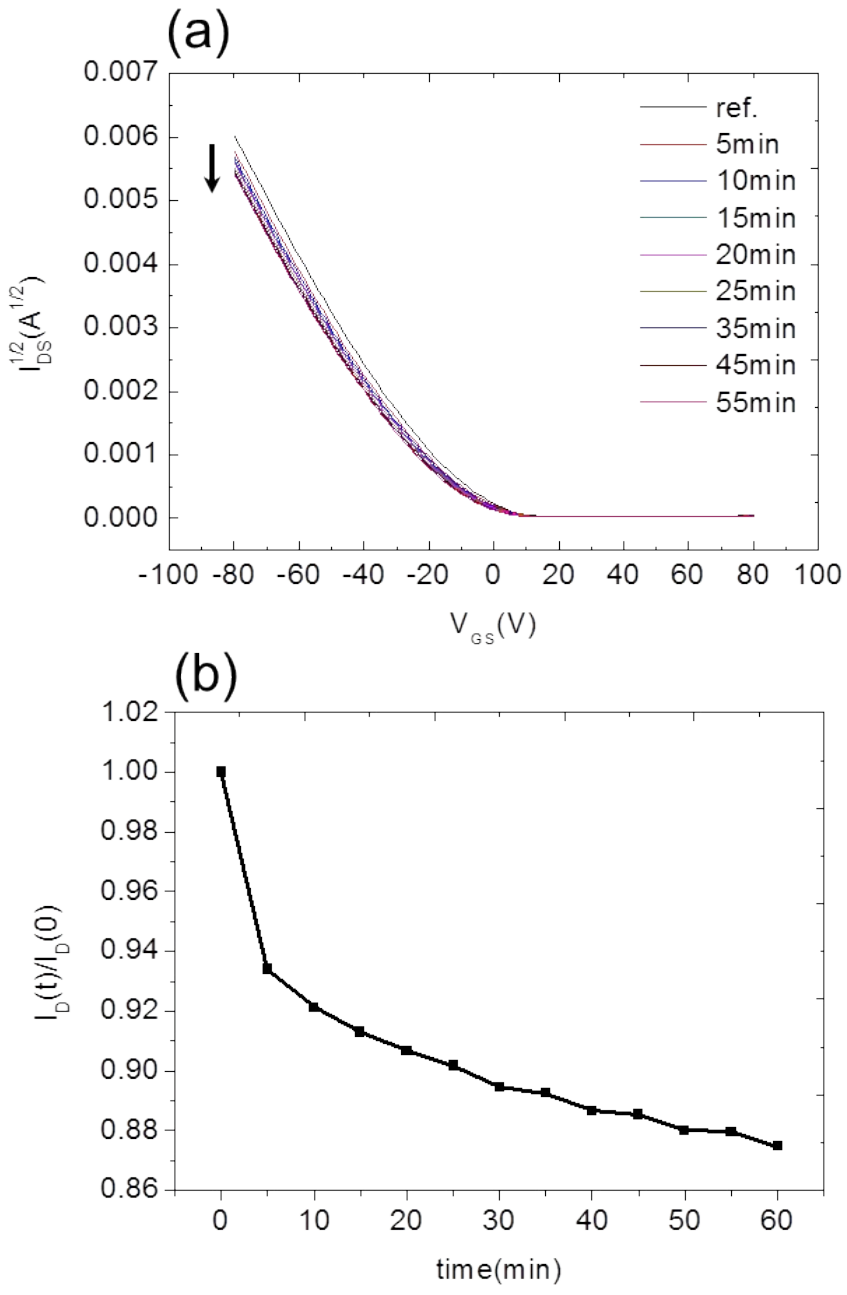
Supporting Figure S2. 2D-GIXRD pattern of pentacene film on SiO_2 dielectric.



Supporting Figure S3. Transfer characteristics of pentacene TFTs with SiO_2 dielectric.



Supporting Figure S4. Capacitances of SFF and SFF-Me dielectrics as a function of frequency.



Supporting Figure S5. (a) Gate bias stability of pentacene TFTs with SiO_2 dielectric. Bias of V_{GS} = –80 V and V_{DS} = –3V were applied on the FETs and transfer characteristics were measured at the given time intervals. Extracted on-current decays from (a) were plotted in (b).